



ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
DC forward current		I_F	60	mA
Surge forward current	$t = 10\text{ }\mu\text{s}$	I_{FSM}	2.5	A
Total power dissipation		P_{diss}	100	mW
OUTPUT				
Collector emitter voltage		V_{CEO}	100	V
Emitter base voltage		V_{EBO}	7	V
Collector current		I_C	50	mA
	$t = 1.0\text{ ms}$	I_C	100	mA
Power dissipation		P_{diss}	150	mW
COUPLER				
Storage temperature range		T_{stg}	-55 to +150	$^{\circ}\text{C}$
Ambient temperature range		T_{amb}	-55 to +100	$^{\circ}\text{C}$
Junction temperature		T_j	100	$^{\circ}\text{C}$
Soldering temperature ⁽¹⁾	Max. 10 s, dip soldering: distance to seating plane $\geq 1.5\text{ mm}$	T_{sld}	260	$^{\circ}\text{C}$

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- ⁽¹⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	I _F = 60 mA		V _F	-	1.25	1.65	V
Breakdown voltage	I _R = 10 μA		V _{BR}	6	-	-	V
Reverse current	V _R = 6 V		I _R	-	0.01	10	μA
Capacitance	V _F = 0 V, f = 1 MHz		C _O	-	25	-	pF
Thermal resistance			R _{thja}	-	750	-	K/W
OUTPUT							
Collector emitter capacitance	f = 1 MHz, V _{CE} = 5 V		C _{CE}	-	6.8	-	pF
Collector base capacitance	f = 1 MHz, V _{CB} = 5 V		C _{CB}	-	8.5	-	pF
Emitter base capacitance	f = 1 MHz, V _{EB} = 5 V		C _{EB}	-	11	-	pF
Thermal resistance			R _{thja}	-	500	-	K/W
Collector emitter leakage current	V _{CE} =10 V	SFH601-1	I _{CEO}	-	2	50	nA
		SFH601-2	I _{CEO}	-	2	50	nA
		SFH601-3	I _{CEO}	-	5	100	nA
		SFH601-4	I _{CEO}	-	5	100	nA
COUPLER							
Saturation voltage collector emitter	I _F = 10 mA, I _C = 2.5 mA		V _{CEsat}	-	0.25	0.4	V
Capacitance (input to output)	V _{I-O} = 0, f = 1 MHz		C _{IO}	-	0.6	-	pF

Note

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F at $V_{CE} = 5.0\text{ V}$	$I_F = 10\text{ mA}$	SFH601-1	CTR	40	-	80	%
		SFH601-2	CTR	63	-	125	%
		SFH601-3	CTR	100	-	200	%
		SFH601-4	CTR	160	-	320	%
	$I_F = 1\text{ mA}$	SFH601-1	CTR	13	30	-	%
		SFH601-2	CTR	22	45	-	%
		SFH601-3	CTR	34	70	-	%
		SFH601-4	CTR	56	90	-	%

Note

- Current transfer ratio and collector emitter leakage current by dash number.

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
NON-SATURATED							
Current	$V_{CC} = 5\text{ V}$, $R_L = 75\ \Omega$		I_F	-	10	-	mA
Rise time	$V_{CC} = 5\text{ V}$, $R_L = 75\ \Omega$		t_r	-	2	-	μs
Fall time	$V_{CC} = 5\text{ V}$, $R_L = 75\ \Omega$		t_f	-	2	-	μs
Turn-on time	$V_{CC} = 5\text{ V}$, $R_L = 75\ \Omega$		t_{on}	-	3	-	μs
Turn-off time	$V_{CC} = 5\text{ V}$, $R_L = 75\ \Omega$		t_{off}	-	2.3	-	μs
SATURATED							
Current		SFH601-1	I_F	-	20	-	mA
		SFH601-2	I_F	-	10	-	mA
		SFH601-3	I_F	-	10	-	mA
		SFH601-4	I_F	-	0.5	-	mA
Rise time		SFH601-1	t_r	-	2	-	μs
		SFH601-2	t_r	-	3	-	μs
		SFH601-3	t_r	-	3	-	μs
		SFH601-4	t_r	-	4.6	-	μs
Fall time		SFH601-1	t_f	-	11	-	μs
		SFH601-2	t_f	-	14	-	μs
		SFH601-3	t_f	-	14	-	μs
		SFH601-4	t_f	-	15	-	μs
Turn-on time		SFH601-1	t_{on}	-	3	-	μs
		SFH601-2	t_{on}	-	4.2	-	μs
		SFH601-3	t_{on}	-	4.2	-	μs
		SFH601-4	t_{on}	-	6	-	μs
Turn-off time		SFH601-1	t_{off}	-	18	-	μs
		SFH601-2	t_{off}	-	23	-	μs
		SFH601-3	t_{off}	-	23	-	μs
		SFH601-4	t_{off}	-	25	-	μs

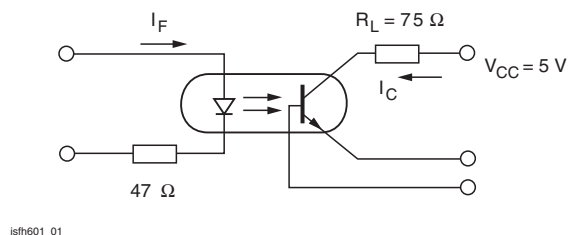


Fig. 1 - Linear Operation (without Saturation)

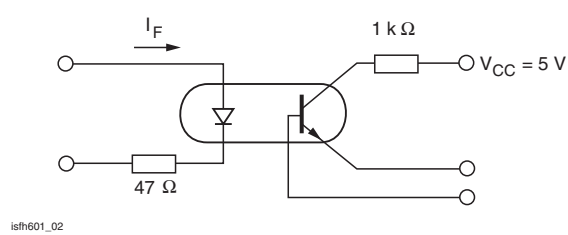


Fig. 2 - Switching Operation (with Saturation)

SAFETY AND INSULATION RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Climatic classification	According to IEC 68 part 1		55 / 100 / 21	
Comparative tracking index		CTI	175	
Maximum rated withstanding isolation voltage	$t = 1 \text{ min}$	V_{ISO}	4420	V_{RMS}
Maximum transient isolation voltage		V_{IOTM}	8000	V
Maximum repetitive peak isolation voltage		V_{IORM}	890	V
Isolation resistance	$V_{\text{IO}} = 500 \text{ V}, T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{12}$	Ω
	$V_{\text{IO}} = 500 \text{ V}, T_{\text{amb}} = 100 \text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{11}$	Ω
Output safety power		P_{SO}	700	mW
Input safety current		I_{SI}	400	mA
Input safety temperature		T_{SI}	175	$^{\circ}\text{C}$
Creepage distance	Standard DIP-4		≥ 7	mm
Clearance distance	Standard DIP-4		≥ 7	mm
Creepage distance	400 mil DIP-4		≥ 8	mm
Clearance distance	400 mil DIP-4		≥ 8	mm
Insulation thickness		DTI	≥ 0.4	mm

Note

- As per IEC 60747-5-5, § 7.4.3.8.2, this optocoupler is suitable for “safe electrical insulation” only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

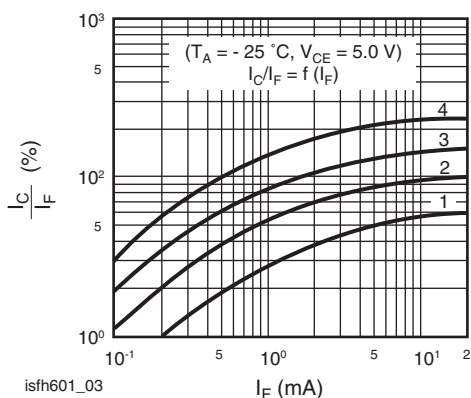
TYPICAL CHARACTERISTICS ($T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified)


Fig. 3 - Current Transfer Ratio vs. Diode Current

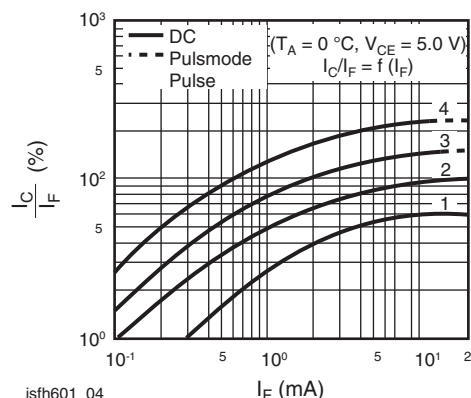


Fig. 4 - Current Transfer Ratio vs. Diode Current

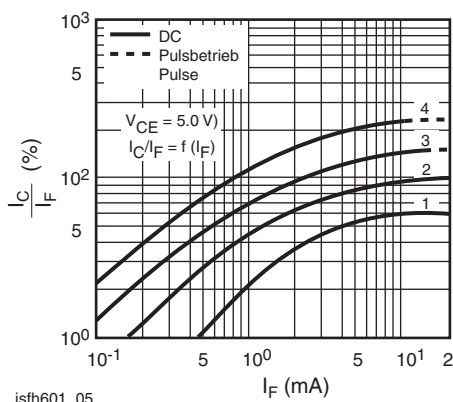


Fig. 5 - Current Transfer Ratio vs. Diode Current

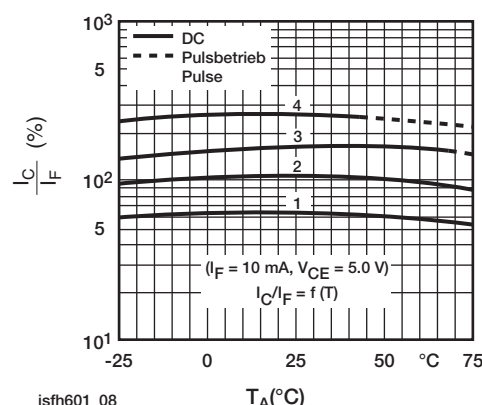


Fig. 8 - Current Transfer Ratio vs. Diode Current

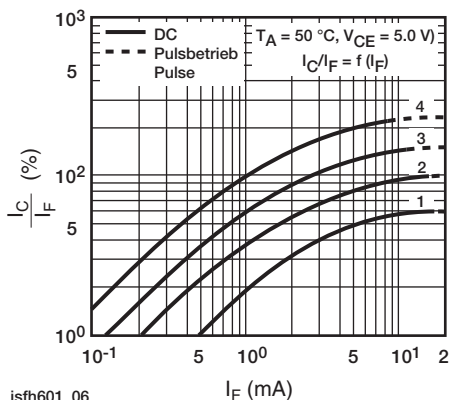


Fig. 6 - Current Transfer Ratio vs. Diode Current

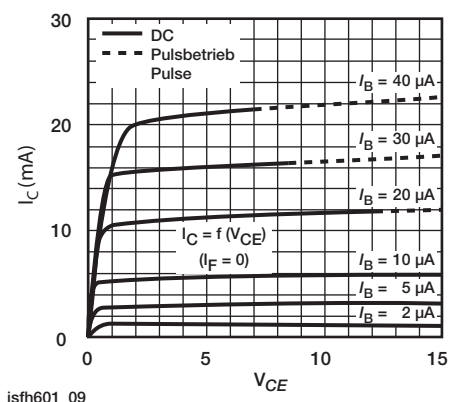


Fig. 9 - Transistor Characteristics

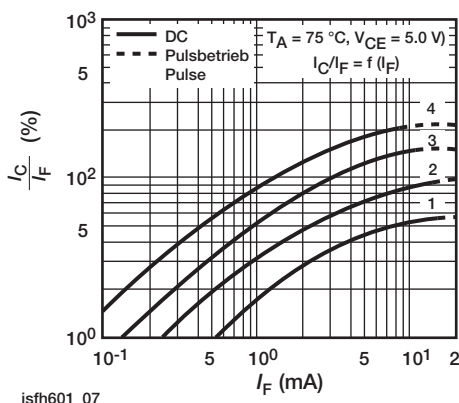


Fig. 7 - Current Transfer Ratio vs. Diode Current

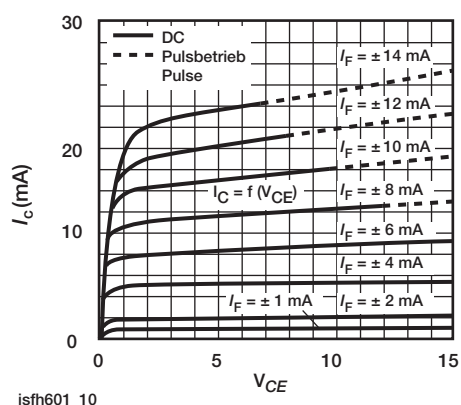


Fig. 10 - Output Characteristics

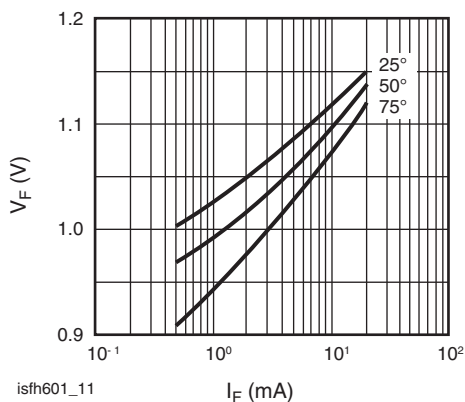


Fig. 11 - Forward Voltage

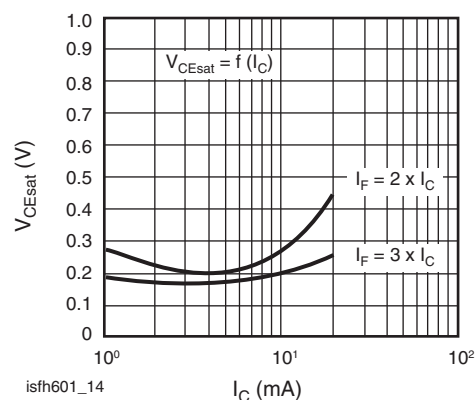


Fig. 14 - Saturation Voltage vs. Collector Current and Modulation Depth SFH601-2

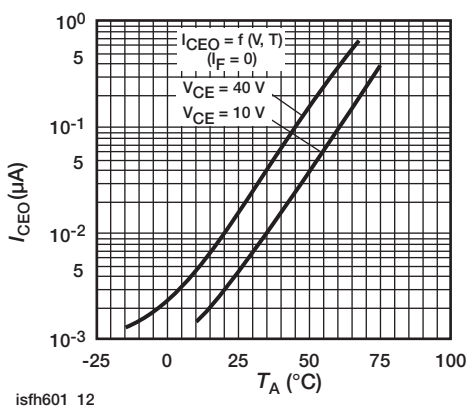


Fig. 12 - Collector Emitter Off-state Current

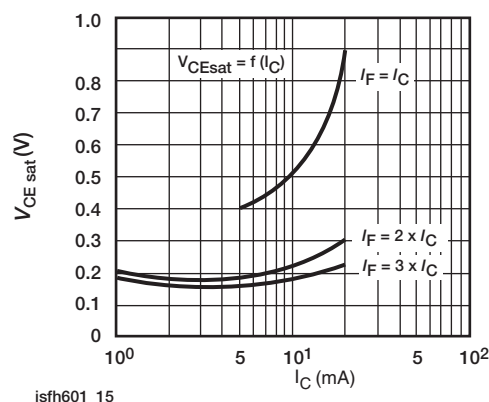


Fig. 15 - Saturation Voltage vs. Collector Current and Modulation Depth SFH601-3

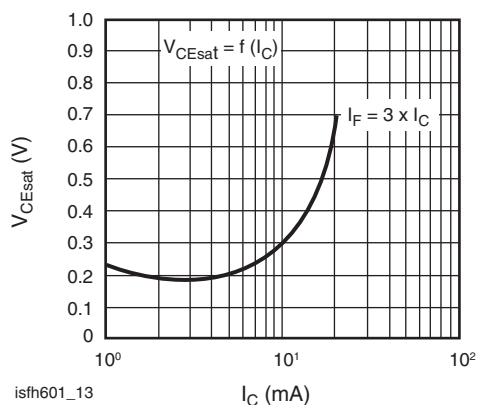


Fig. 13 - Saturation Voltage vs. Collector Current and Modulation Depth SFH601-1

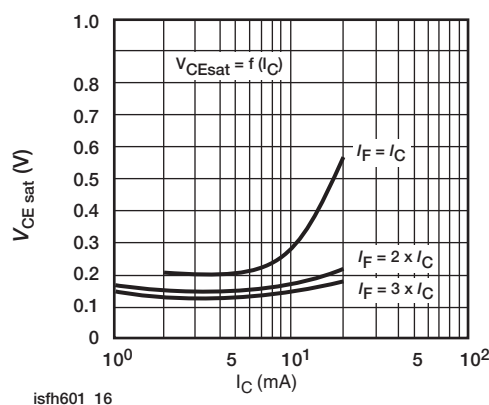


Fig. 16 - Saturation Voltage vs. Collector Current and Modulation Depth SFH601-4

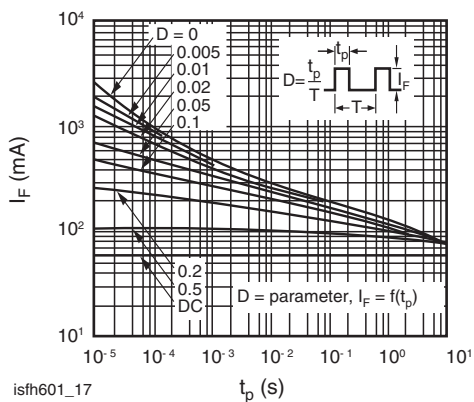


Fig. 17 - Permissible Pulse Load

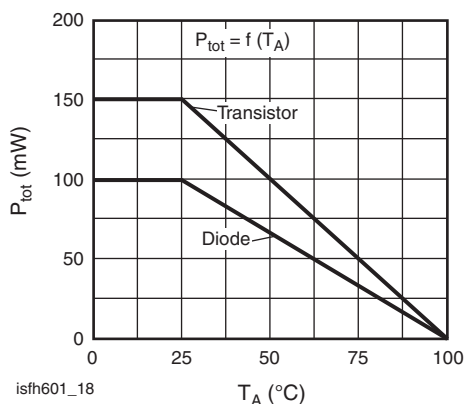


Fig. 18 - Permissible Power Dissipation for Transistor and Diode

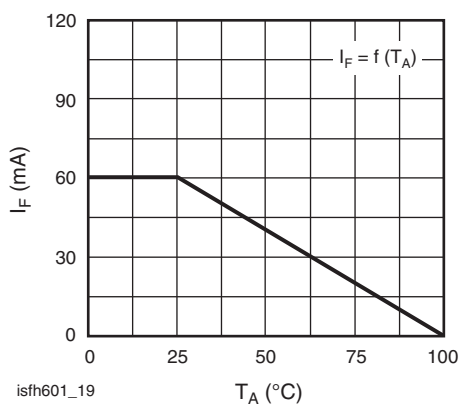
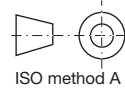
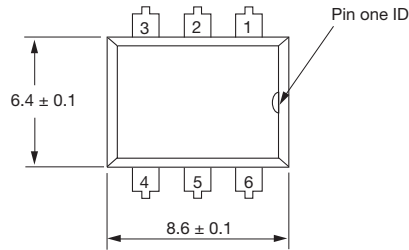


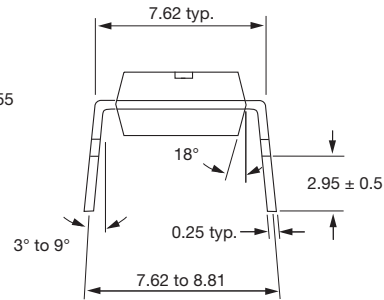
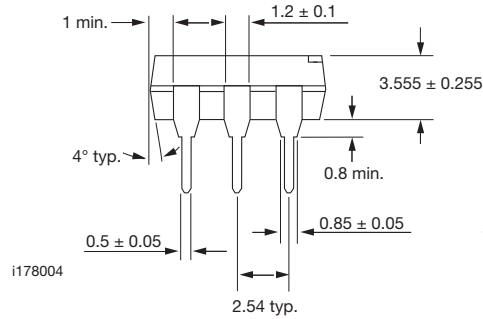
Fig. 19 - Permissible Forward Current Diode



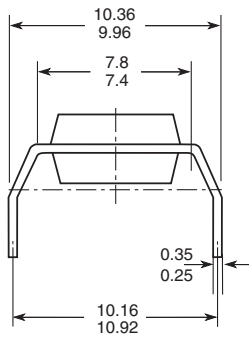
PACKAGE DIMENSIONS in inches (millimeters)



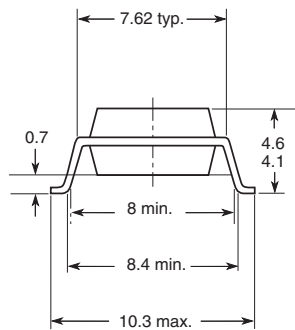
ISO method A



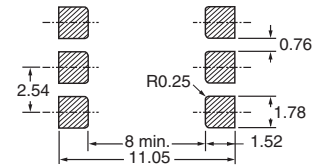
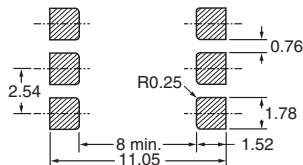
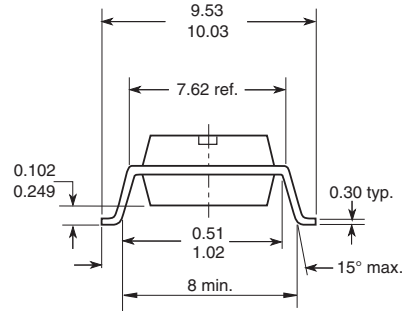
Option 6



Option 7



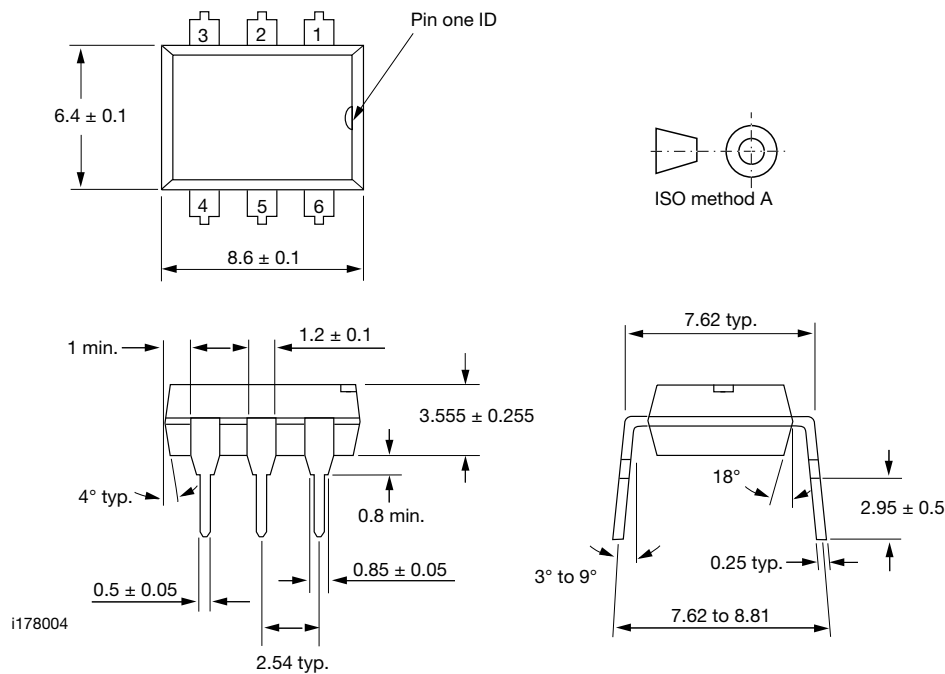
Option 9



18450-16

DIP-6A

PACKAGE DIMENSIONS in inches (millimeters)



Note

The information in this document provides generic information but for specific information on a product the appropriate product datasheet should be used.



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